TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MAR2245FK

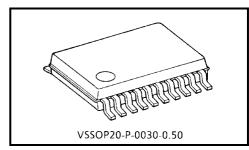
Low-Voltage Octal Bus Transceiver with 3.6 V Tolerant Inputs and Outputs

The TC7MAR2245FK is a high performance CMOS octal bus transceiver. Designed for use in 1.8, 2.5 or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V$.

The direction of data transmission is determined by the level of the DIR inputs. The \overline{OE} inputs can be used to disable the device so that the busses are effectively isolated.

The $26 \cdot \Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.



Weight: 0.03 g (typ.)

All inputs are equipped with protection circuits against static discharge.

Features

- 26-Ω series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation:

 $\begin{aligned} t_{pd} &= 4.4 \text{ ns (max) (V}_{CC} = 3.0 \text{~-} 3.6 \text{ V)} \\ t_{pd} &= 5.6 \text{ ns (max) (V}_{CC} = 2.3 \text{~-} 2.7 \text{ V)} \\ t_{pd} &= 9.8 \text{ ns (max) (V}_{CC} = 1.8 \text{ V)} \end{aligned}$

3.6 V tolerant inputs and outputs.

• Output current: $IOH/IOL = \pm 12 \text{ mA (min)} (VCC = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 8 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $IOH/IOL = \pm 4 \text{ mA (min) (VCC} = 1.8 \text{ V)}$

- ESD performance:
 - ESD performance.

Machine model > $\pm 200 \text{ V}$ Human body model > $\pm 2000 \text{ V}$

Latch-up performance: ±300 mA

- Package: VSSOP (US20)
- Bidirectional interface between 2.5 V and 3.3 V signals. (*1)
- Power down protection is provided on all inputs and outputs. (*2)
- Supports live insertion/withdrawal (*3)
 - *1: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.
 - *2: All floating (high impedance) bus terminal must have their input level fixed by means of pull up or pull down resistors.
 - *3: To ensure the high-impedance state during power up or power down, OE should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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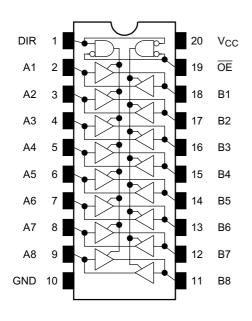
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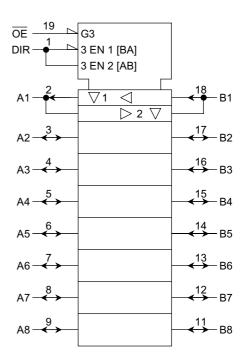
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Pin Assignment (top view)

TOSHIBA



IEC Logic Symbol



Truth Table

Inp	Inputs Outputs		Function			
ŌĒ	DIR	Outputs	A-Bus	B-Bus		
L	L	A = B	Output	Input		
L	Н	B = A	Input	Output		
Н	Х	Z	Z			

X: Don't care

Z: High impedance



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage (DIR, $\overline{\text{OE}}$)	V _{IN}	-0.5~4.6	٧
DC bus I/O voltage	V _{I/O}	-0.5~4.6 (Note1)	V
Do bus 1/O Voltage	V I/O	-0.5~V _{CC} + 0.5 (Note2)	V
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note3)	mA
DC output current	lout	±50	mA
Power dissipation	PD	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note1: Off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	1.8~3.6	V	
Supply voltage	VCC	1.2~3.6 (Note4)	V	
Input voltage (DIR, $\overline{\mbox{OE}}$)	V _{IN}	-0.3~3.6	V	
Bus I/O voltage	V/	0~3.6 (Note5)	V	
Bus I/O voltage	V _{I/O}	0~V _{CC} (Note6)	V	
		±12 (Note7)		
Output current	I _{OH} /I _{OL}	±8 (Note8)	mA	
		±4 (Note9)	·	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V	

Note4: Data retention only

Note5: Off-state

Note6: High or low state Note7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note9: $V_{CC} = 1.8 \text{ V}$

Note10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$



Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
la anticalta ara	High level	V _{IH}		_	2.7~3.6	2.0	_	V
Input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	V
				$I_{OH} = -100 \mu A$	2.7~3.6	V _{CC} - 0.2		
	High level	Voh	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.7	2.2	_	
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	_	
Output voltage				I _{OH} = -12 mA	3.0	2.2		V
	Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2	
				I _{OL} = 6 mA	2.7	_	0.4	
				$I_{OL} = 8 \text{ mA}$	3.0	_	0.55	
				I _{OL} = 12 mA	3.0	_	0.8	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
2 state output off	atata aurrant	1	$V_{IN} = V_{IH}$ or V_{IL}		2.7~3.6		±10.0	
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.1~3.0	_	±10.0	μΑ
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Quiescent supply current		laa	V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
Quiescent supply	current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7~3.6	_	±20.0	μΑ
Increase in I _{CC} pe	r input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6	_	750	

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Innut voltage	High level	V _{IH}		_	2.3~2.7	1.6	_	V	
Input voltage	Low level	V _{IL}		_	2.3~2.7	_	0.7	V	
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_		
	High level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -4 \text{ mA}$	2.3	2.0	_		
			V_{OL} $V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -6 mA	2.3	1.8	_	V	
Output voltage	out voltage			$I_{OH} = -8 \text{ mA}$	2.3	1.7	_		
					$I_{OL} = 100 \mu A$	2.3~2.7	_	0.2	
	Low level	V_{OL}			$V_{IN} = V_{IH} \ or \ V_{IL}$	I _{OL} = 6 mA	2.3	_	0.4
				I _{OL} = 8 mA	2.3	_	0.6	i	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V	•	2.3~2.7	_	±5.0	μΑ	
3-state output off-state current I _O		lo-	V _{IN} = V _{IH} or V _{IL}		2.3~2.7		±10.0		
		102	V _{OUT} = 0~3.6 V		2.3~2.1		±10.0	μΑ	
Power off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ	
Quiescent supply	current	loo	V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	пΔ	
Quiescent supply	Curtil	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μΑ	



DC Characteristics (Ta = -40~85°C, 1.8 V ≤ V_{CC} < 2.3 V)

Characteri	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V _{IH}		_	1.8~2.3	0.7× V _{CC}	_	V
Input voltage	Low level	V _{IL}		_	1.8~2.3	_	0.2× V _{CC}	V
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage				I _{OH} = -4 mA	1.8	1.4	_	V
	Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	1.8	_	0.2	
	Low level	VOL		I _{OL} = 4 mA	1.8	_	0.3	
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8		±5.0	μΑ
3-state output off-st	ate current	I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8		±10.0	μА
Power off leakage of	urrent	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Quiescent supply co	ırrent	loo	$V_{IN} = V_{CC}$ or GND		1.8		20.0	μА
Quiescent supply co	an c nt	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μΑ

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	pol Test Condition		Min	Max	Unit
			V _{CC} (V)	1.5	9.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	5.6	ns
	t _{pHL}		3.3 ± 0.3	0.6	4.4	
	4		1.8	1.5	9.8	
3-state output enable time	t _{pZL} t _{pZH}	Figure 1, Figure 3	2.5 ± 0.2	8.0	6.6	ns
			3.3 ± 0.3	0.6	5.0	
	4		1.8	1.5	8.5	
3-state output disable time		t _{pLZ} Figure 1, Figure 3	2.5 ± 0.2	8.0	4.7	ns
	t _{pHZ}		3.3 ± 0.3	0.6	4.2	
			1.8	_	0.5	
Output to output skew		(Note11)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		3.3 ± 0.3	_	0.5	

For $C_L = 50 \ pF$, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

 $(t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \ t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|)$



Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition			Tun	Unit
Characteristics	Symbol	rest Condition		V _{CC} (V)	Тур.	Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	1.8	0.15	
Quiet output maximum dynamic V _{OL}	V_{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	3.3	0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	1.8	-0.15	
Quiet output minimum dynamic V _{OL}	V_{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	2.5	-0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	1.8	1.55	
Quiet output minimum dynamic V _{OH}	V_{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote12)	3.3	2.65	

Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol Test Condition		_		Тур.	Unit
Onaractoristics	Cymbol	rest condition		V _{CC} (V)	ıyρ.	Oille
Input capacitance	C _{IN}	DIR, OE		1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	An, Bn		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{\text{IN}} = 10 \text{ MHz}$ (No	ote13)	1.8, 2.5, 3.3	20	pF

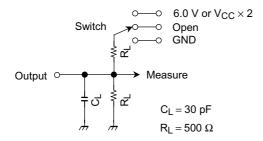
Note13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$



AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	6.0 V V _{CC} × 2	$@V_{CC} = 3.3 \pm 0.3 \text{ V} \\ @V_{CC} = 2.5 \pm 0.2 \text{ V} \\ @V_{CC} = 1.8 \text{ V}$	
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

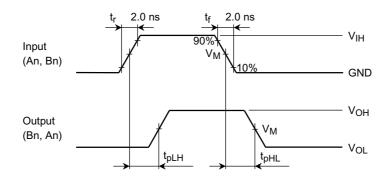


Figure 2 t_{pLH}, t_{pHL}

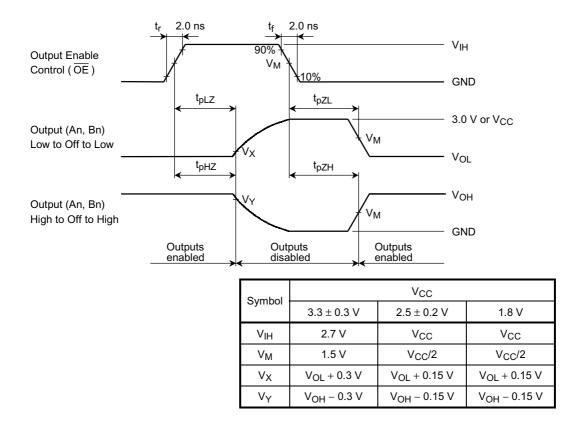
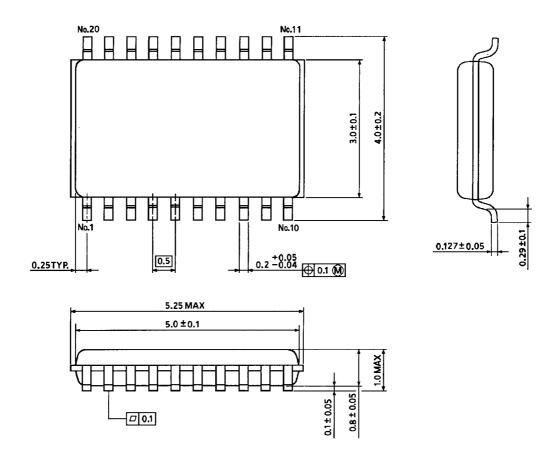


Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Package Dimensions



Weight: 0.03 g (typ.)